

Dual N-Channel Enhancement Power MOSFET

PRODUCT SUMMARY GENERAL DESCRIPTION 20 V V_{DS} DP8205 uses advanced trench technology to provide excellent R_{DS(ON)}, I_D (at V_{GS} =4.5V) 5.0A low gate charge and operation with gate voltages as low as 2.5V. This $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 29mΩ device is suitable for use as a Battery protection or in other Switching $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) < 34mΩ application. SOT23-6 D1 (2, 5) D₂ (2, 5) G1(6) G2(4) S1(1) S2(3) Absolute Maximum Ratings TA=25°C unless otherwise noted Parameter Symbol Limit Unit 20 V **Drain-Source Voltage** V_{DS} V_{GS} Gate-Source Voltage ±12 V Drain Current-Continuous @ T₁=25℃ 5 I_{D} А Pulsed^b 20 I_{DM} А Drain-Sourse Diode Forward Current^a 2.5 А ls 1.25 Maximum Power Dissipation^a P_{D} W Operating Junction and Storage Temperature Range T_J,T_{STG} -55 To 150 °C **Thermal Characteristic** Parameter Symbol Limit Unit Thermal Resistance, Junction-to-Ambient ^a 100 °C/W $R_{\theta JA}$ Thermal Resistance, Junction to Lead 65 °C/W $R_{\theta JL}$



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ELECTRICAL CHARACTERISTICS (TA=25°Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Турс	Мах	Unit
Off Characteristics		I	1	1	1	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	±100	nA
On Characteristics				$\mathcal{I}_{\mathcal{N}}$		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =4.5A	14	20	29	mΩ
		V _{GS} =2.5V, I _D =3.5A	17	27	34	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =7A	-	17.7	-	S
Dynamic Characteristics		. 6				
Input Capacitance	C _{lss}	V _{DS} =8V,	-	802	-	pF
Output Capacitance	C _{oss}	V _{GS} =0V,	-	153	-	pF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	122	-	pF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =10V,	-	18	-	nS
Turn-on Rise Time	t,	I _D =1A	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =4.5V, R_{GEN} =10 Ω ,	-	43.8	-	nS
Turn-Off Fall Time	t _f	$R_L=10\Omega$	-	20	-	nS
Total Gate Charge	Qg	V _{DS} =10V,	-	10.5	-	nC
Gate-Source Charge	Q _{gs}	I _D =4A,	-	2	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =4.5V	-	2.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =1.7A	-	-	1.2	V

Notes:

a. Surface Mounted on FR4 Board ,T<10 sec ;

b. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

c. Guaranteed by Design, not subject to production testing.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

2025/4/15 DP8205 REV3.55 EN

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DP8205













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